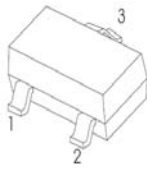
FEATURE

- High dense cell design for extremely low $R_{DS(ON)}$.
- Exceptional on-resistance and maximum DC current capability

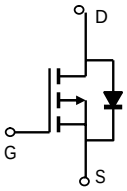
P-Channel Enhancement Mode Field Effect Transistor

SOT-23



1. GATE
2. SOURCE
3. DRAIN

Equivalent Circuit



ORDERING INFORMATION

Type No.	Marking	Package Code
LX3401A	A19T	SOT-23

Maximum ratings (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	-4.2	A
Power Dissipation	P_D	350	mW
Thermal Resistance from Junction to Ambient (t<5s)	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

Electrical characteristics (Ta=25℃ unless otherwise noted)

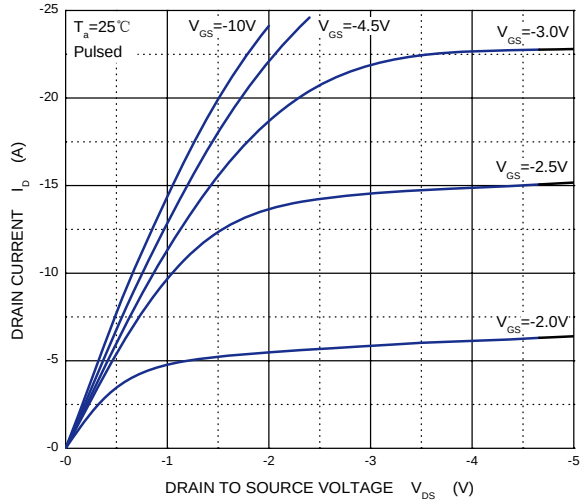
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-24V,V_{GS} = 0V			-1	μA
Gate-source leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±100	nA
On characteristics						
Drain-source on-resistance (note 1)	$R_{DS(on)}$	V_{GS} =-10V, I_D =-4.2A			65	mΩ
		V_{GS} =-4.5V, I_D =-4A			75	mΩ
		V_{GS} =-2.5V,I_D=-1A			90	mΩ
Forward tranconductance (note 1)	g_{FS}	V_{DS} =-5V, I_D =-5A	7			S
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.7		-1.3	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	V_{DS} =-15V,V_{GS} =0V,f =1MHz		954		pF
Output capacitance	C_{oss}			115		pF
Reverse transfer capacitance	C_{rss}			77		pF
Switching characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=-10V,V_{DS}=-15V, R_L=3.6Ω,R_{GEN}=6Ω			6.3	ns
Turn-on rise time	t_r				3.2	ns
Turn-off delay time	$t_{d(off)}$				38.2	ns
Turn-off fall Time	t_f				12	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 1)	V_{SD}	I_S=-1A,V_{GS}=0V			-1	V

Note :

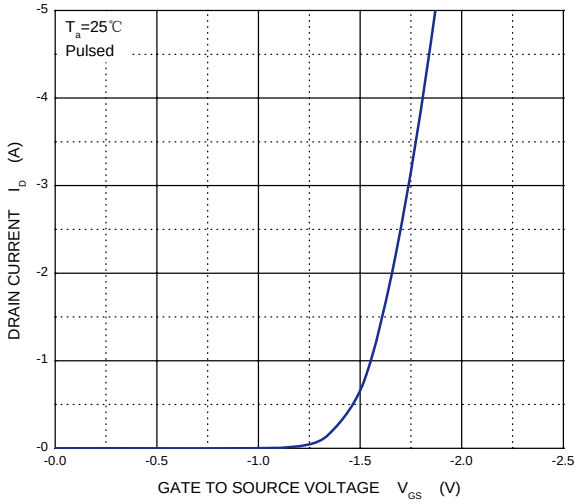
1. Pulse Test : Pulse width≤300μs, duty cycle≤2%.
2. These parameters have no way to verify.

Typical Characteristics

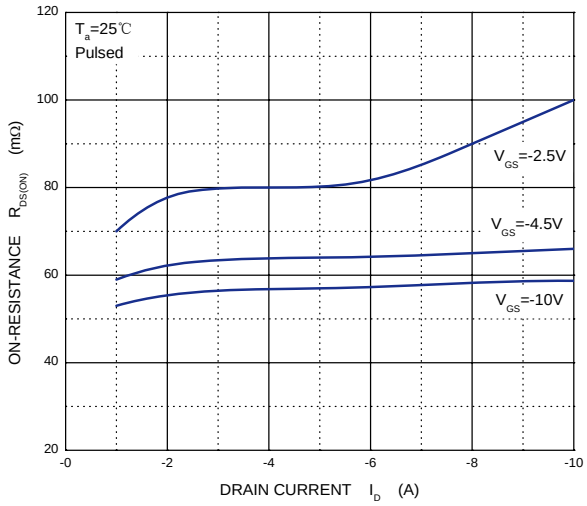
Output Characteristics



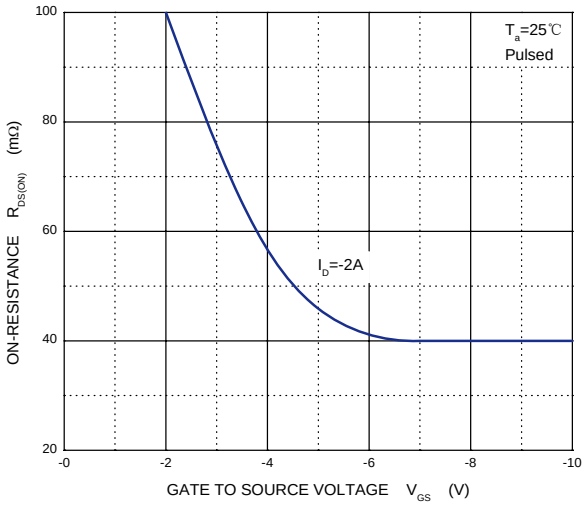
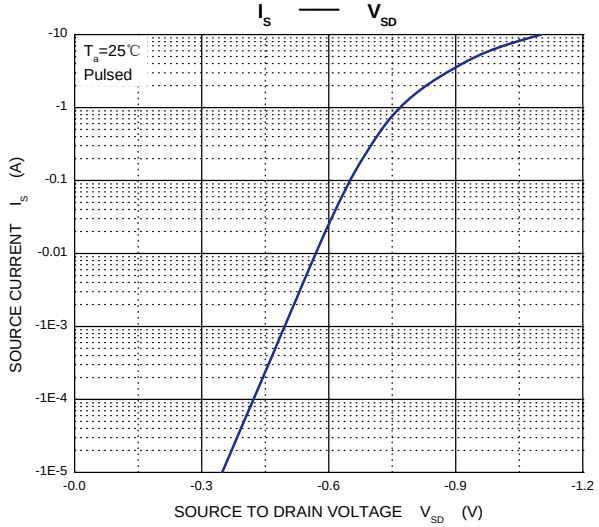
Transfer Characteristics



$R_{DS(ON)}$ —— I_D



$R_{DS(ON)}$ —— V_{GS}



I_S —— V_{SD}